

1、Description

Glass passivated, sensitive gate triacs in a plastic envelope, intended for use in general purpose bi-directional switching and phase control applications, where high sensitivity is required in all four quadrants.


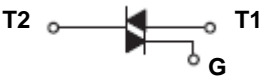
2、Applications

- Motor control
- Industrial and domestic lighting
- Heating
- Static switching

3、Features

- Blocking voltage to 800V
- On-state RMS current to 4 A
- Ultra low gate trigger current
- Low cost package.

4、Pinning information

PIN	Description	Simplified outline	Symbol
1	main terminal 1 (T1)	 TO-126	
2	main terminal 2 (T2)		
3	gate (G)		
tab	main terminal		

5、Quick reference data

SYMBOL	PARAMETER	MAX	UNIT
V_{DRM} V_{DRM}	Repetitive peak off-state voltages	800	V
$I_{T(RMS)}$	RMS on-state current	4	A
I_{TSM}	Non-repetitive peak on-state current	40	A

6、Thermal characteristics

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Thermal Resistance, Junction to Case	<i>in free air</i>	-	-	3.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	<i>in free air</i>	-	-	75	°C/W
T_L	Maximum Lead Temperature for Soldering Purposes for 10 Seconds	<i>in free air</i>	-	-	260	°C

7、Limiting value

Limiting values in accordance with the Maximum System(IEC 134).

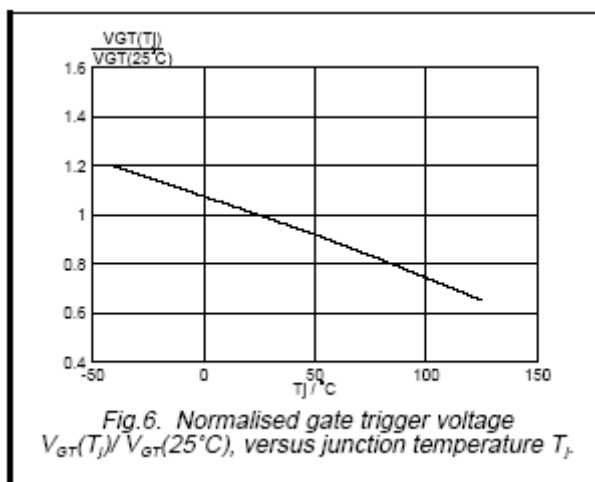
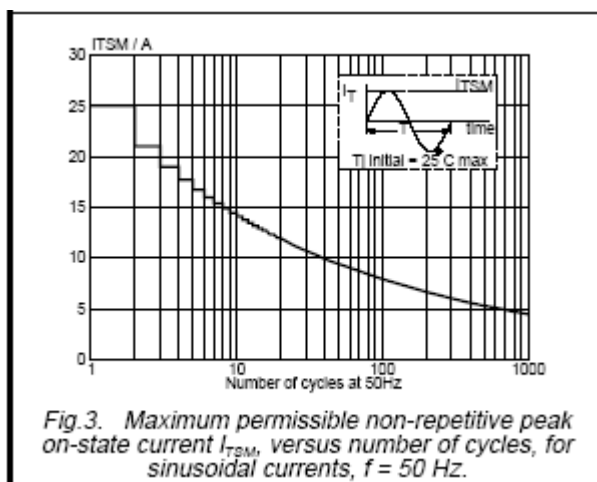
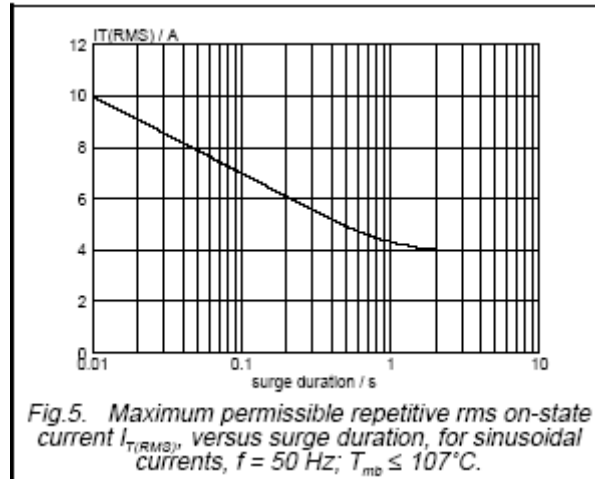
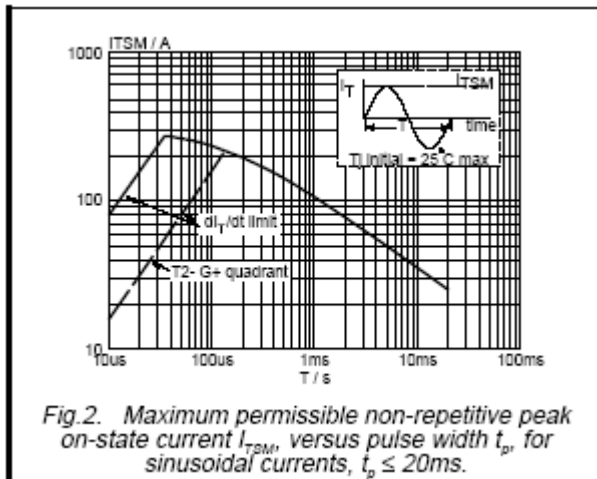
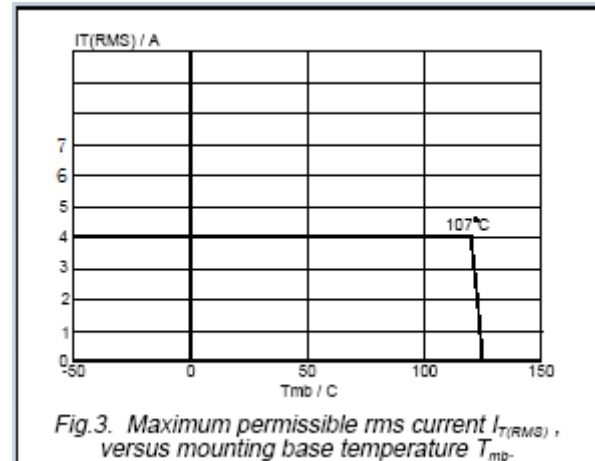
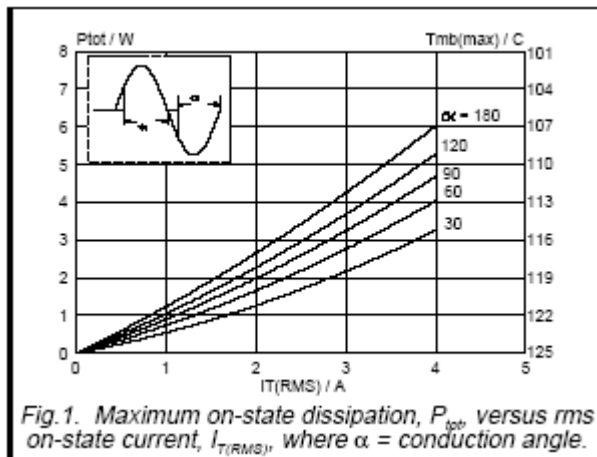
SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{DRM} V_{RRM}	Repetitive peak off-state voltages		-	600	V
$I_{T(RMS)}$	RMS on-state current	Full Cycle Sine Wave 50 to 60 Hz (TC = 85°C)	-	4	A
I_{TSM}	Non-repetitive peak Surge current	One Full cycle, 60 Hz, $T_J = +110^{\circ}\text{C}$	-	40	A
I^2t	I^2t for fusing	$t = 8.3\text{ms}$	-	3.7	A^2s
V_{GM}	Peak gate voltage	Pulse Width $\leq 1.0\text{ }\mu\text{s}$, TC = 85°C	-	5	V
P_{GM}	Peak gate power	Pulse Width $\leq 1.0\text{ }\mu\text{s}$, TC = 85°C	-	10	W
$P_{G(AV)}$	Average gate power	Pulse Width $\leq 1.0\text{ }\mu\text{s}$, TC = 85°C	-	0.5	W
T_{stg}	Storage temperature		-40	150	°C
T_J	Operating junction temperature		-40	110	°C

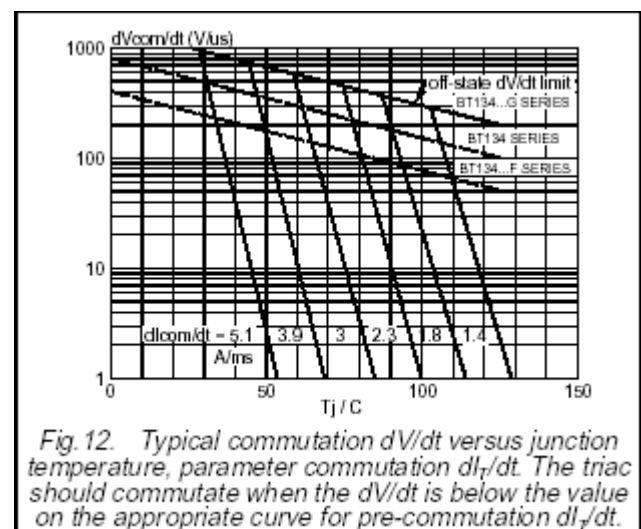
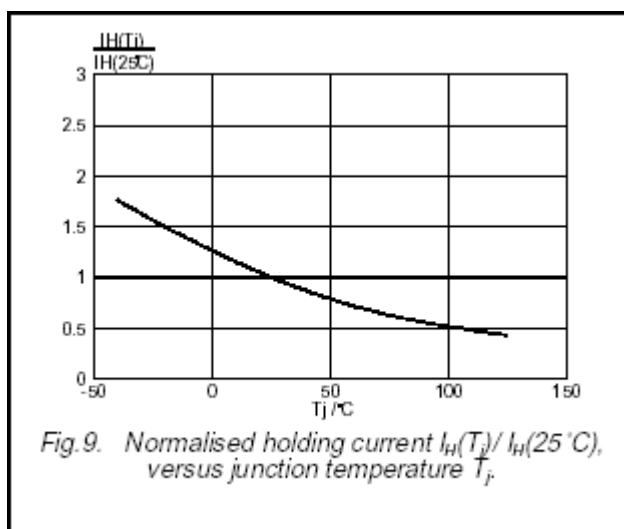
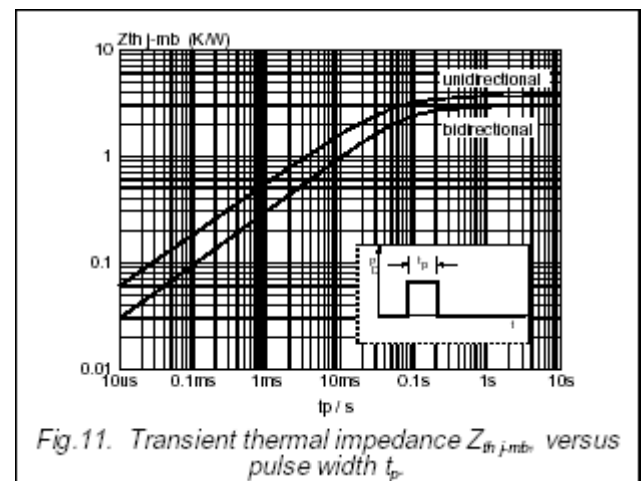
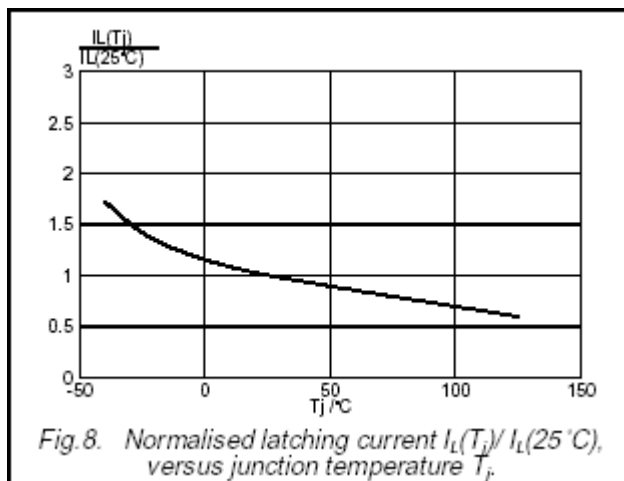
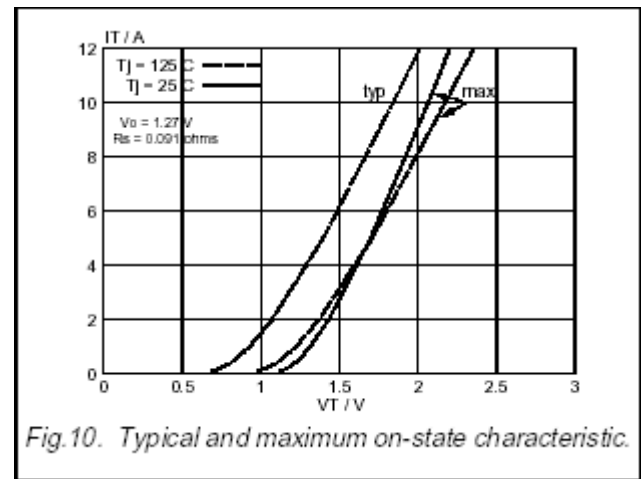
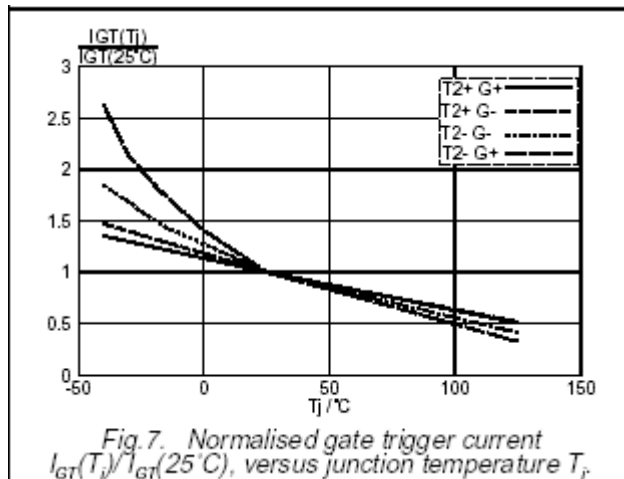
8、Characteristics

$T_J = 25^{\circ}\text{C}$ unless otherwise stated

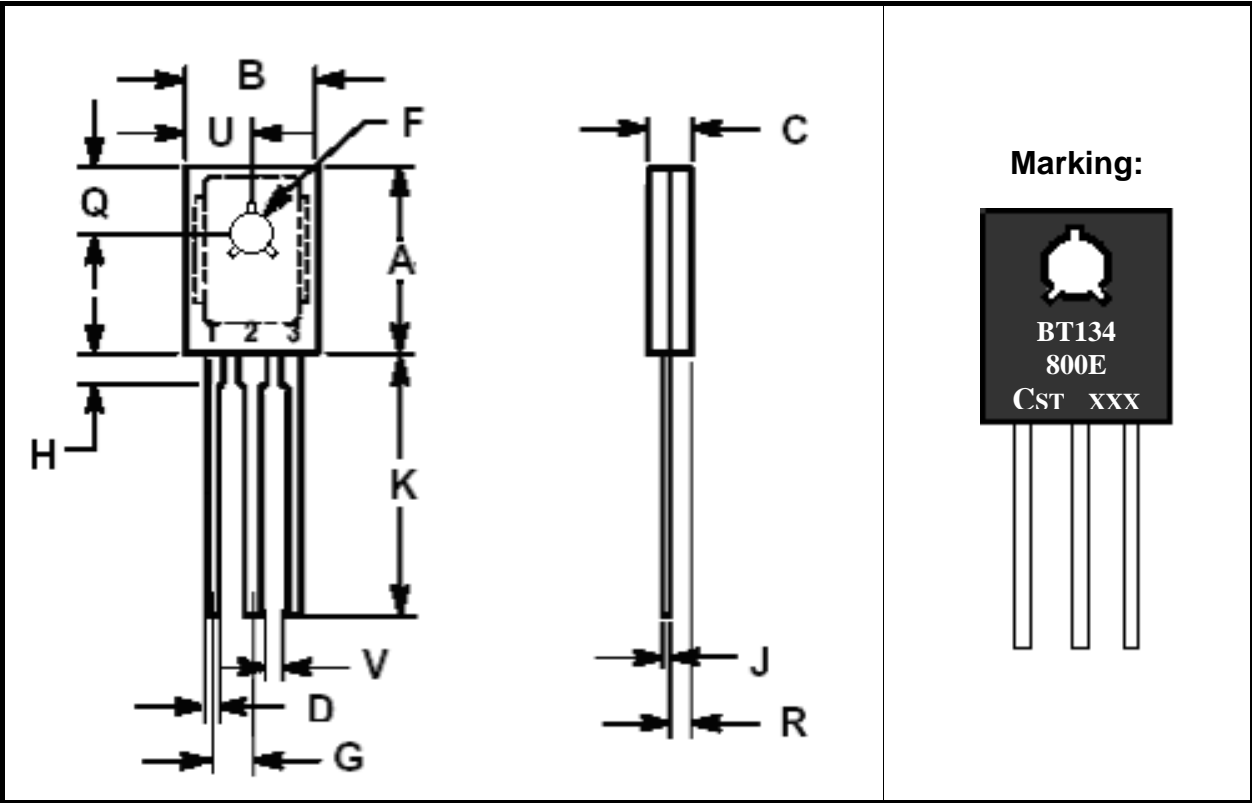
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Static characteristics						
I_{GT}	Gate trigger current	$V_D = 12\text{ V}$; $I_T = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G- T2- G+	- - - -	3 3 3 8	10 10 10 25	mA mA mA mA
I_L	Latching current	$V_D = 12\text{ V}$; $I_{GT} = 0.1\text{ A}$ T2+ G+ T2+ G- T2- G- T2- G+	- - - -	1.5 5 1.0 3.0	15 20 15 20	mA mA mA mA
I_H	Holding current	Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current $\leq 1\text{ Adc}$ $T_J = 25^{\circ}\text{C}$ $T_J = -40^{\circ}\text{C}$	- -	- -	15 30	mA
V_{TM}	On-state voltage	$I_{TM} = \pm 6\text{ A Peak}$	-	1.4	2	V
V_{GT}	Gate trigger voltage (Continuous dc)	Main Terminal Voltage = 12 Vdc, $R_L = 100\text{ Ohms}$, $T_J = -40^{\circ}\text{C}$ All Quadrants	-	1.4	2.5	V
V_{GD}	Gate Non-Trigger Voltage	Main Terminal Voltage = 12 Vdc, $R_L = 100\text{ Ohms}$, $T_J = 110^{\circ}\text{C}$ All Quadrants	0.2	-	-	V
Dynamic Characteristics						
$dV/dt(c)$	Critical rate of rise of off-state voltage	V_{DRM} , $T_J = 85^{\circ}\text{C}$, Gate Open, $I_{TM} = 5.7\text{ A}$, Exponential Waveform, Commutating $di/dt = 2.0\text{ A/ms}$	-	5	-	V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM} = 14\text{ Adc}$, $I_{GT} = 100\text{ mAdc}$	-	1.5	-	μs

9、Electrical Characteristics Curve





10、Package outline(TO-126)



DIM	Inches			Millimeters		
	Min	Type	Max	Min	Type	Max
A	0.419	-	0.429	10.65	-	10.89
B	0.284	-	0.312	7.22	-	7.92
C	0.091	0.100	0.109	2.30	2.54	2.76
K	0.520	-	0.598	13.20	-	15.20
D	0.025	0.029	0.031	0.64	0.73	0.80
J	0.011	-	0.020	0.28	-	0.52
G	0.087	0.091	0.094	2.20	2.30	2.40
V	0.040	-	-	1.02	-	-
F	0.115	0.122	0.130	2.93	3.10	3.30
U	0.142	-	0.157	3.60	-	4.00
Q	0.151	-	0.163	3.83	-	4.13
H	0.071	0.102	0.114	1.80	2.6	2.90
R	0.045	-	0.065	1.15	-	1.65